

### 54F/74F251A 8-Input Multiplexer with TRI-STATE® Outputs

#### **General Description**

# The 'F251A is a high-speed 8-input digital multiplexer. It provides, in one package, the ability to select one bit of data from up to eight sources. It can be used as a universal function generator to generate any logic function of four variables. Both assertion and negation outputs are provided.

#### **Features**

- Multifunctional capability
- On-chip select logic decoding
- Inverting and non-inverting TRI-STATE outputs

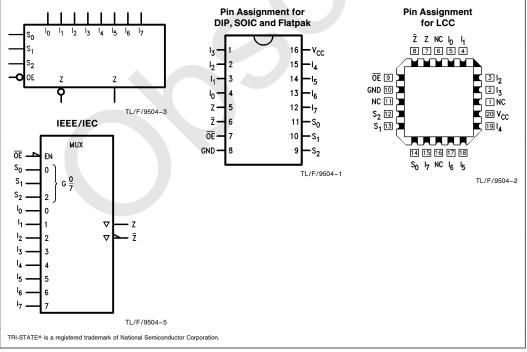
Commercial	Military	Package Number	Package Description			
74F251APC		N16E	16-Lead (0.300" Wide) Molded Dual-In-Line			
	54F251ADM (Note 2)	J16A	16-Lead Ceramic Dual-In-Line			
74F251ASC (Note 1)		M16A	16-Lead (0.150" Wide) Molded Small Outline, JEDEC			
74F251ASJ (Note 1)		M16D	16-Lead (0.300" Wide) Molded Small Outline, EIAJ			
	54F251AFM (Note 2)	W16A	16-Lead Cerpack			
	54F251ALL (Note 2)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C			

Note 1: Devices also available in 13" reel. Use suffix = SCX and SJX.

Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

#### **Logic Symbols**

#### **Connection Diagrams**



#### **Unit Loading/Fan Out**

		54F/74F			
Pin Names	Description	U.L. HIGH/LOW	Input I <sub>IH</sub> /I <sub>IL</sub> Output I <sub>OH</sub> /I <sub>OL</sub>		
S <sub>0</sub> -S <sub>2</sub>	Select Inputs	1.0/1.0	20 μA/-0.6 mA		
OË _	TRI-STATE Output Enable Input (Active LOW)	1.0/1.0	20 μA/-0.6 mA		
I <sub>0</sub> -I <sub>7</sub>	Multiplexer Inputs	1.0/1.0	20 μA/-0.6 mA		
Z	TRI-STATE Multiplexer Output	150/40 (33.3)	-3 mA/24 mA (20 mA)		
Z	Complementary TRI-STATE Multiplexer Output	150/40 (33.3)	-3 mA/24 mA (20 mA)		

#### **Functional Description**

This device is a logical implementation of a single-pole, 8position switch with the switch position controlled by the state of three Select inputs, So, S1, S2. Both assertion and negation outputs are provided. The Output Enable input (OE) is active LOW. When it is activated, the logic function provided at the output is:

$$\begin{split} Z &= \overline{OE} \bullet (I_0 \bullet \overline{S}_0 \bullet \overline{S}_1 \bullet \overline{S}_2 + I_1 \bullet S_0 \bullet \overline{S}_1 \bullet \overline{S}_2 + \\ &\quad I_2 \bullet \overline{S}_0 \bullet S_1 \bullet \overline{S}_2 + I_3 \bullet S_0 \bullet S_1 \bullet \overline{S}_2 + \\ &\quad I_4 \bullet \overline{S}_0 \bullet \overline{S}_1 \bullet S_2 + I_5 \bullet S_0 \bullet \overline{S}_1 \bullet S_2 + \\ &\quad I_6 \bullet \overline{S}_0 \bullet S_1 \bullet S_2 + I_7 \bullet S_0 \bullet S_1 \bullet S_2) \end{split}$$

When the Output Enable is HIGH, both outputs are in the high impedance (High Z) state. This feature allows multiplexer expansion by tying the outputs of up to 128 devices together. When the outputs of the TRI-STATE devices are tied together, all but one device must be in the high impedance state to avoid high currents that would exceed the maximum ratings. The Output Enable signals should be designed to ensure there is no overlap in the active LOW portion of the enable voltages.

#### **Truth Table**

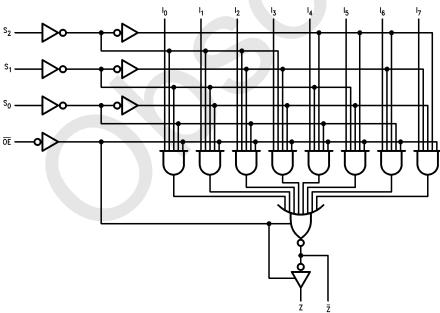
	Inp	Outputs			
ŌĒ	S <sub>2</sub>	S <sub>1</sub>	S <sub>0</sub>	Z	Z
Н	Х	X	Χ	Z	Z
L	L	L	L	Ī <sub>0</sub>	I <sub>0</sub>
L	L	L	Н	Ī <sub>1</sub>	l <sub>1</sub>
L	L	Н	L	Ī <sub>2</sub>	l <sub>2</sub>
L	L	Н	Н	Ī <sub>3</sub>	l <sub>3</sub>
L	Н	L	L	Ī <sub>4</sub>	14
L	Н	L	H	Ī <sub>4</sub> Ī <sub>5</sub>	l <sub>5</sub>
L	Н	Н	L	Ī <sub>6</sub>	l <sub>6</sub>
L	Н	Н	Н	Ī <sub>7</sub>	l <sub>7</sub>

H = HIGH Voltage Level
L = LOW Voltage Level

X = Immaterial

Z = High Impedance

#### **Logic Diagram**



TL/F/9504-4

Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

#### **Absolute Maximum Ratings** (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{lll} \mbox{Storage Temperature} & -65^{\circ}\mbox{C to } + 150^{\circ}\mbox{C} \\ \mbox{Ambient Temperature under Bias} & -55^{\circ}\mbox{C to } + 125^{\circ}\mbox{C} \\ \mbox{Junction Temperature under Bias} & -55^{\circ}\mbox{C to } + 175^{\circ}\mbox{C} \\ \mbox{Plastic} & -55^{\circ}\mbox{C to } + 150^{\circ}\mbox{C} \\ \end{array}$ 

V<sub>CC</sub> Pin Potential to

Voltage Applied to Output

in HIGH State (with  $V_{CC} = 0V$ )

 $\begin{array}{lll} \text{Standard Output} & -0.5 \text{V to V}_{\text{CC}} \\ \text{TRI-STATE Output} & -0.5 \text{V to } +5.5 \text{V} \end{array}$ 

Current Applied to Output

in LOW State (Max)  $\qquad \qquad \text{twice the rated I}_{\text{OL}} \, (\text{mA})$ 

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

# Recommended Operating Conditions

Free Air Ambient Temperature

Supply Voltage

Military +4.5V to +5.5V Commercial +4.5V to +5.5V

#### **DC Electrical Characteristics**

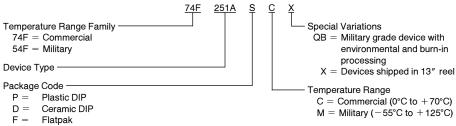
Symbol	Parameter -		54F/74F			Units	V <sub>CC</sub>	Conditions	
Symbol			Min	Тур	Max	Units	VCC	Conditions	
V <sub>IH</sub>	Input HIGH Voltage	2.0			٧		Recognized as a HIGH Signal		
V <sub>IL</sub>	Input LOW Voltage				0.8	٧		Recognized as a LOW Signal	
V <sub>CD</sub>	Input Clamp Diode Volta	ge			-1.2	V	Min	$I_{\text{IN}} = -18  \text{mA}$	
V <sub>OH</sub>	Output HIGH Voltage	54F 10% V <sub>CC</sub> 54F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub> 74F 5% V <sub>CC</sub> 74F 5% V <sub>CC</sub>	2.5 2.4 2.5 2.4 2.7 2.7			V	Min	$I_{OH} = -1 \text{ mA}$ $I_{OH} = -3 \text{ mA}$ $I_{OH} = -1 \text{ mA}$ $I_{OH} = -3 \text{ mA}$	
V <sub>OL</sub>	Output LOW Voltage	54F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub>			0.5 0.5	V	Min	I <sub>OL</sub> = 20 mA I <sub>OL</sub> = 24 mA	
I <sub>IH</sub>	Input HIGH Current	54F 74F			20.0 5.0	μΑ	Max	$V_{\text{IN}} = 2.7V$	
I <sub>BVI</sub>	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	V <sub>IN</sub> = 7.0V	
I <sub>CEX</sub>	Output HIGH Leakage Current	54F 74F			250 50	μΑ	Max	$V_{OUT} = V_{CC}$	
$V_{\text{ID}}$	Input Leakage Test	74F	4.75			٧	0.0	$I_{\text{ID}} = 1.9  \mu\text{A}$ All Other Pins Grounded	
I <sub>OD</sub>	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V <sub>IOD</sub> = 150 mV All Other Pins Grounded	
I <sub>IL</sub>	Input LOW Current				-0.6	mA	Max	$V_{IN} = 0.5V$	
lozh	Output Leakage Current				50	μΑ	Max	V <sub>OUT</sub> = 2.7V	
lozL	Output Leakage Current				-50	μΑ	Max	V <sub>OUT</sub> = 0.5V	
los	Output Short-Circuit Current		-60		-150	mA	Max	V <sub>OUT</sub> = 0V	
I <sub>ZZ</sub>	Bus Drainage Test				500	μΑ	0.0V	V <sub>OUT</sub> = 5.25V	
ICCL	Power Supply Current			15	22	mA	Max	$V_O = LOW$	
I <sub>CCZ</sub>	Power Supply Current			16	24	mA	Max	V <sub>O</sub> = HIGH Z	

#### **AC Electrical Characteristics**

Symbol Parameter		74F		54F  T <sub>A</sub> , V <sub>CC</sub> = Mil  C <sub>L</sub> = 50 pF		74F  T <sub>A</sub> , V <sub>CC</sub> = Com C <sub>L</sub> = 50 pF		Units	
	Parameter	$\begin{aligned} \textbf{T}_{\textbf{A}} &=  +25^{\circ}\textbf{C} \\ \textbf{V}_{\textbf{CC}} &=  +5.0\textbf{V} \\ \textbf{C}_{\textbf{L}} &=  50\textbf{pF} \end{aligned}$							
		Min	Тур	Max	Min	Max	Min	Max	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay $S_n$ to $\overline{Z}$	3.5 3.2	6.0 5.0	9.0 7.5	3.5 3.2	11.5 8.0	3.5 3.2	9.5 7.5	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay S <sub>n</sub> to Z	4.5 4.0	7.5 6.0	10.5 8.5	3.5 3.0	14.0 10.5	4.5 4.0	12.5 9.0	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay $I_n$ to $\overline{Z}$	3.0 1.5	5.0 2.5	6.5 4.0	2.5 1.5	8.0 6.0	3.0 1.5	7.0 5.0	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay In to Z	3.5 3.5	5.0 5.5	7.0 7.0	2.5 3.5	9.0 9.0	2.5 3.5	8.0 7.5	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time	2.5 2.5	4.3 4.3	6.0 6.0	2.0 2.5	7.0 7.5	2.5 2.5	7.0 6.5	ns
t <sub>PHZ</sub>	Output Disable Time $\overline{OE}$ to $\overline{Z}$	2.5 1.5	4.0 3.0	5.5 4.5	2.5 1.5	6.0 5.0	2.5 1.5	6.0 4.5	113
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time OE to Z	3.5 3.5	5.0 5.5	7.0 7.5	3.0 3.5	8.5 9.0	3.0 3.5	7.5 8.0	ns
t <sub>PHZ</sub>	Output Disable Time OE to Z	2.0 1.5	3.8 3.0	5.5 4.5	2.0 1.5	5.5 5.5	2.0 1.5	5.5 4.5	



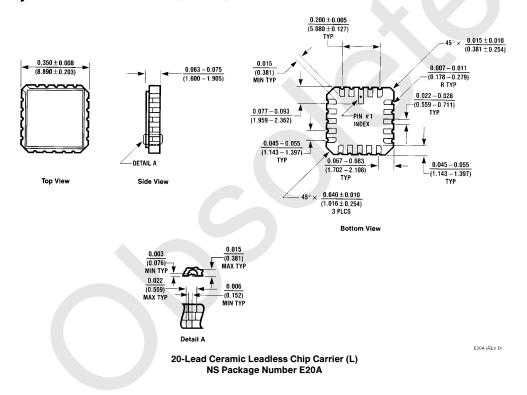
The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

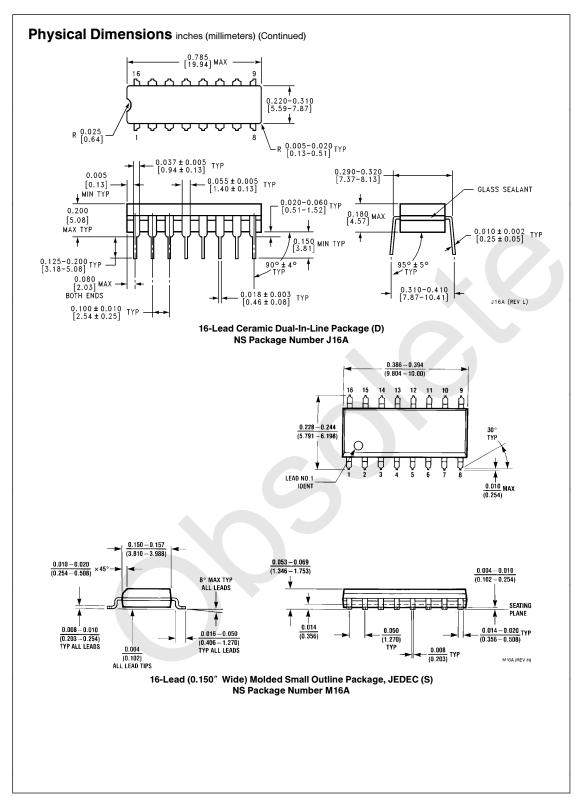


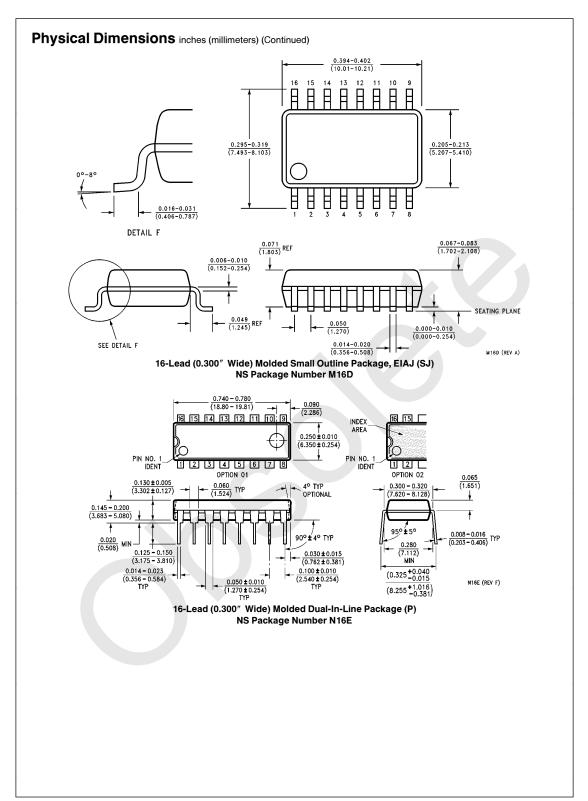
L = Leadless Chip Carrier (LCC) S = Small Outline SOIC JEDEC

SJ = Small Outline SOIC EIAJ

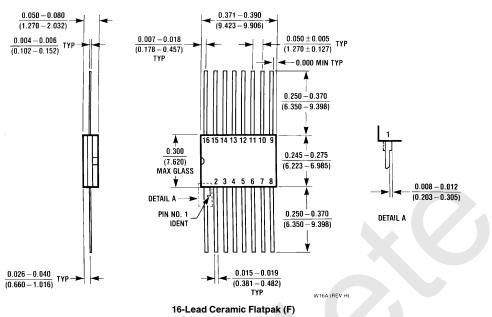
#### Physical Dimensions inches (millimeters)







#### Physical Dimensions inches (millimeters) (Continued)



## NS Package Number W16A

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National Semiconductor Corporation 2900 Semiconductor Drive P.O. Box 58090 Santa Clara, CA 95052-8090 Tel: 1(800) 272-9959 TWX: (910) 339-9240 National Semiconductor GmbH Livry-Gargan-Str. 10 D-82256 Fürstenfeldbruck Germany Tel: (81-41) 35-0 Telex: 527649

Fax: (81-41) 35-1

ductor National Semiconductor Japan Ltd.
Sumitomo Chemical Engineering Center Bldg. 7F
1-7-1, Nakase, Mihama-Ku Chiba-City, Ciba Prefecture 261

r National Semiconductor Hong Kong Ltd. 13th Floor, Straight Block, Ocean Centre, 5 Canton Rd. Tsimshatsui, Kowloon Hong Kong Tel: (852) 2737-1600 Fax: (852) 2736-9960 National Semiconductores Do Brazil Ltda. Rue Deputado Lacorda Franco 120-3A Sao Paulo-SP Brazil 05418-000 Tel: (55-11) 212-5066 Telex: 391-1131931 NSBR BR Fax: (55-11) 212-1181 National Semiconductor (Australia) Pty, Ltd. Building 16 Business Park Drive Monash Business Park Nottinghill, Melbourne Victoria 3168 Australia Tel: (3) 558-9999 Fax: (3) 558-9999